

Studies on Diamond-like Carbon Coated GEMs and Ceramic GEMs

RD51 Collaboration Meeting
CERN

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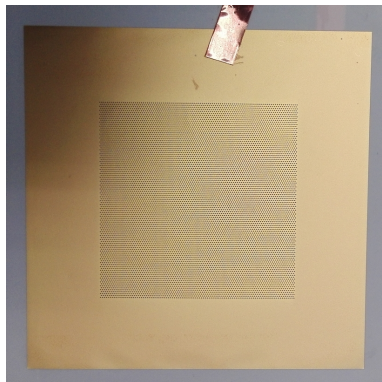
1 Ceramic GEMs

- Test Chamber and Measurement Parameters
- Measurements and Characterization
- Results
- Summary of Ceramic GEMs

2 Diamond-like Carbon Coated GEMs

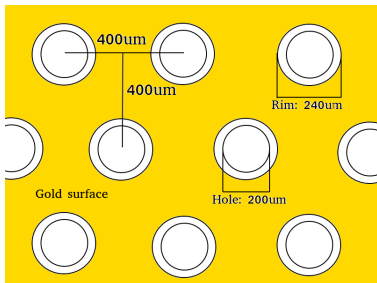
- Coating Procedure
- FIB Analysis
- Gain of DLC GEMs
- Summary of DLC GEMs

- Motivation for the use of ceramic: **Higher tolerance for discharges.**
- Produced by a Japanese Company named " **KOA Corporation** "
- Holes made by tipping

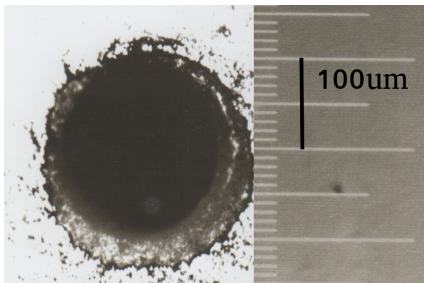


Ceramic GEM

- Two batches of GEMs
 - ▶ **First batch: Without rim** around the holes. Caused discharges at low voltages
 - ▶ **Second batch: Rim included.** Decreased probability of discharges. Only the second batch of GEMs are characterized.



Sketch of a ceramic GEM

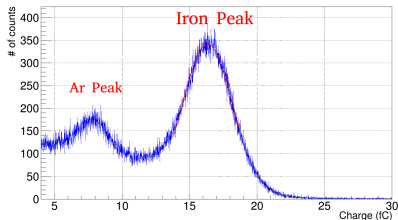


A picture of a hole in a ceramic GEM

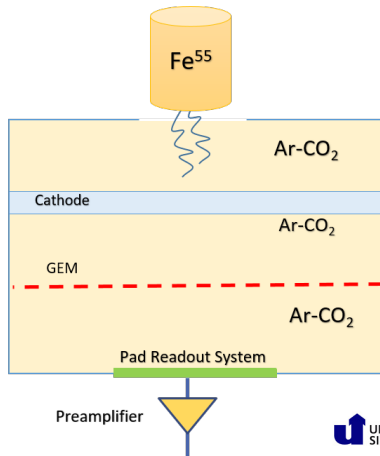
Properties	ceramic	CERN
Size	50mm × 50mm	50mm × 50mm
Thickness	120μm	50μm
Conductor	Silver, Nickel and Gold	Copper
Insulator	Ceramic	Kapton
Holes diameter	200μm (straight)	50 – 70μm (conic)
Pitch	400μm	140μm
Ceramic body	Glass-Alumina composite	n/a

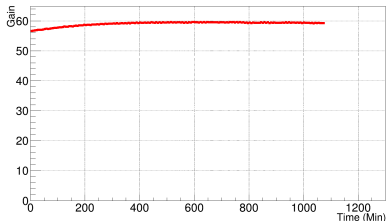
Test Chamber in Siegen

- Small chamber (**120 mm × 184 mm**) to measure the gain of GEMs.
- Gas mixture: **Ar – CO₂ (80% – 20%)** mixture.
- 5.9 keV **X-ray source (⁵⁵Fe)** for primary ionization.
- Drift field: **0.5 kV/cm**, induction field: **2kV/cm**.
- Pressure: **Air pressure**
- Temperature: **Room temperature**
- Multi Channel Analyzer (MCA) Spectra

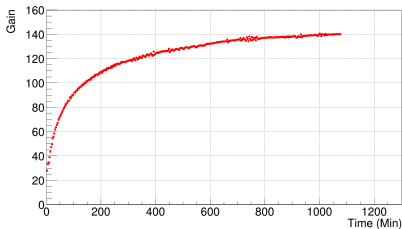


Signal with 2 peaks (Argon escape peak and ⁵⁵Fe peak).



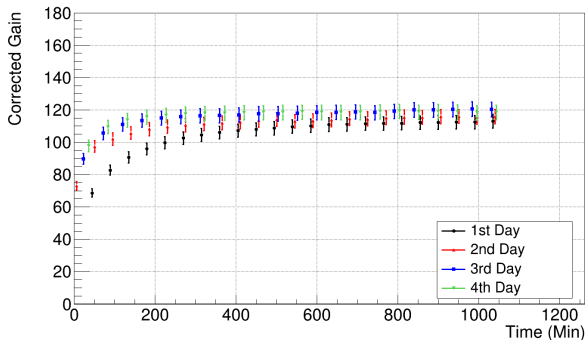


Long time measurement with
CERN GEM



Long time measurement with
ceramic GEM

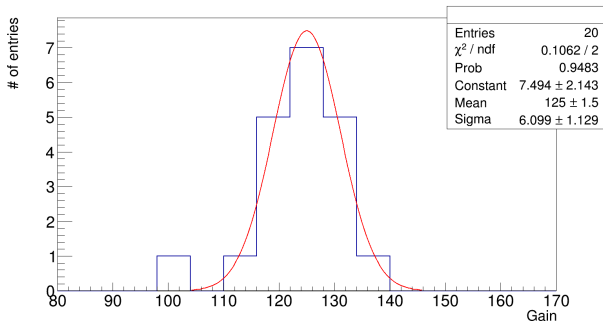
- The first important result of ceramic GEM: **Charge up effect.**
 - ▶ CERN GEM gain starts already from **95% of maximum gain**
 - ▶ Gain stabilization of a ceramic GEM takes **hours.**



Long time measurements **after T/P correction** at 1 atm and 300 K.

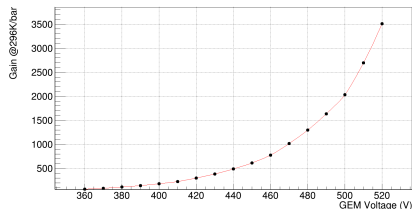
Time required for	1st Day	2nd Day	3rd Day	4th Day	3 Days Later
90% of max gain	258 min	132 min	93 min	69 min	189 min
95% of max gain	414 min	276 min	192 min	117 min	297 min

- Second important result: **Conditioning**
 - ▶ Increase of gain stabilization with consecutive measurements

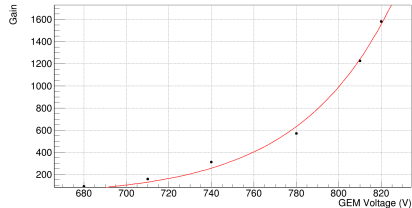


Distribution of gains from different measurements taken for 4 months of period

- Mean of the distribution of the corrected gains (at 1 atm and 300 K) from different measurements: **125**
- Relative width: $\sigma/\mu = 4.9\%$



CERN GEM voltage vs gain.
1 atm and 300 K

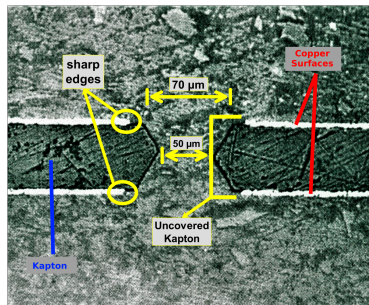


Ceramic GEM voltage vs. gain
~1 atm and ~300 K

- Achievable maximum voltage without discharges
 - ▶ for CERN GEM: **520 V**
 - ▶ for ceramic GEM: **820 V**
- Gain at achievable maximum voltage without discharges
 - ▶ for CERN GEM: **~3500**
 - ▶ for ceramic GEM: **~1600**

- CERN GEM and ceramic GEM measurements have been performed.
- Repeatability check of ceramic GEMs
 - ▶ < 5% deviation between different measurements within 1σ
- **Charging up effect observed.**
- **Conditioning observed.**
- **Lower maximum safe gain.**
- Ceramic GEM studies have been terminated.

- Motivation
 - ▶ Reduce of **discharge probability** by coating **sharp edges** and **kapton inside the holes**
 - ▶ Establishment of **well defined electric field within the hole**
 - ▶ Increase of **maximum safe gain voltage** (and gain)
- Four batches of coating with different thicknesses and speeds
 - ▶ **50 nm fast**, **50 nm**, **100 nm**, **300 nm**



Cross section of a GEM

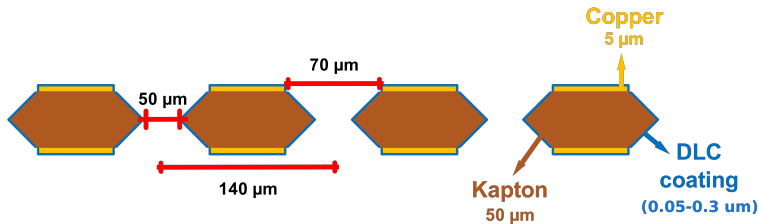
GEM	C. Speed	Thickness (nm)
SICON50f	fast	50
SICON50	normal	50
SICON100	normal	100
SICON300	normal	300

The list of DLC coated GEMs. There are four coated GEMs for each type of coating.

DLC Coating Procedure

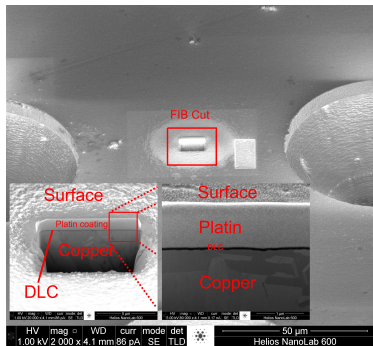
- Coatings done by **Fraunhofer-Institut für Schicht- und Oberflächentechnik** using Plasma assisted Chemical Vapor Deposition (PACVD) procedure.
 - Hexamethyldisiloxane (HMDSO)** for **a-C:H:Si:O (SICON)** coating
 - High electric field to break HMDSO into fragments to grow diamond-like bonding
- Thickness control by deposition time

Coating material	Chemical deposition	Element Concentration			
		C	H	Si	O
HMDSO	a-C:H:Si:O	41-43	22-23	23-24	10-11

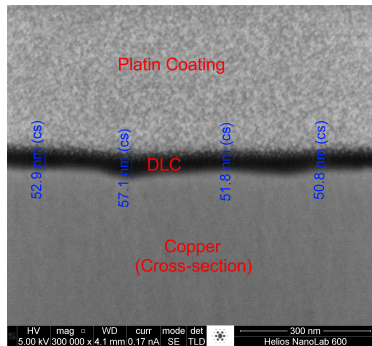


Schematic Cross section of a DLC GEM*

- **FIB (Focused Ion Beam)** analysis by Micro- and Nanoanalytics at Uni Siegen (Prof. Dr. Butz)
 - ▶ Coating of **platin-organic compounds** to increase contrast
 - ▶ Confirmed **the thickness** on surface of the GEM: **~50nm**

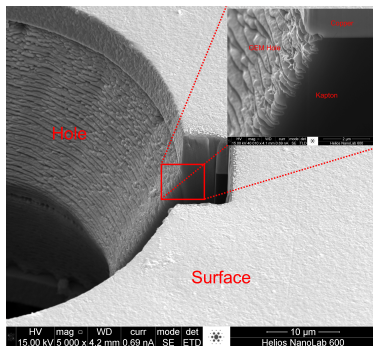


FIB image from surface of the GEM.

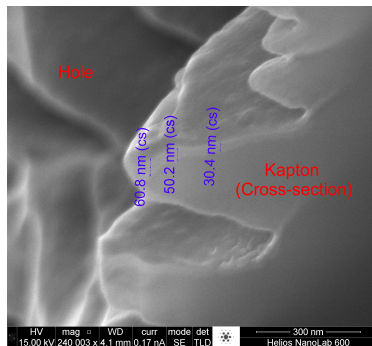


FIB image with thickness measurement.

- The coating thickness measurement not possible due to **non-homogeneity of the inner wall of the hole**
- Rough surface inside the hole due to etching of the holes
- Confirmed **the existence of the DLC** on the wall of the hole by EDX



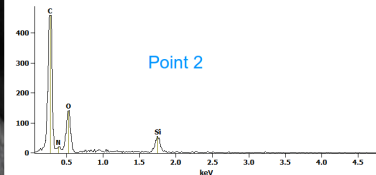
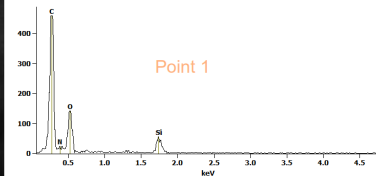
FIB image from a hole of the GEM.



FIB image inside the GEM hole with a presumable coating.

Thickness Measurements (in the Holes)

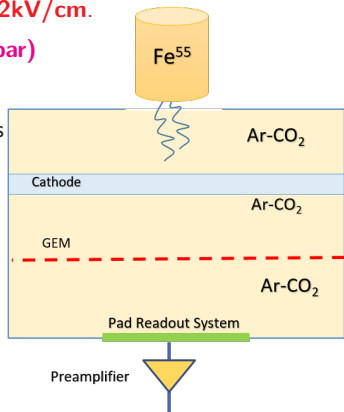
- The coating thickness measurement not possible due to **non-homogeneity of the inner wall of the hole**
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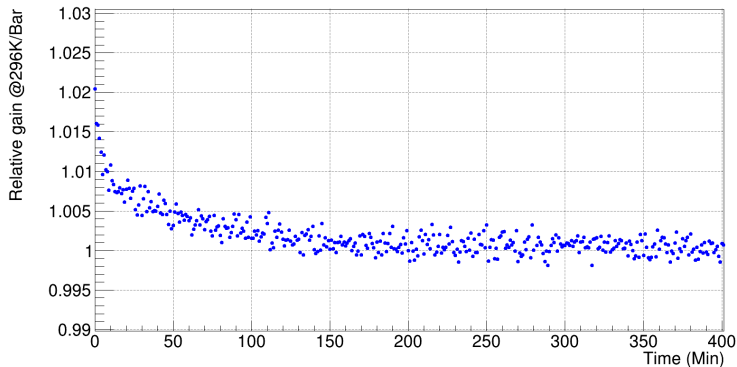


SEM image with EDX analysis

- Small chamber (**120 mm × 184 mm**) to measure the gain of GEMs.
- Gas mixture: **Ar – CO₂ (80% – 20%)** mixture.
- 5.9 keV **X-ray source** (**⁵⁵Fe**) for primary ionization.
- Drift field: **0.5 kV/cm**, induction field: **2kV/cm**.
- Pressure: **1 atm (1013.25 mbar ±1 mbar)**
- Temperature: **~ 300K ±1K**
- **Corrected gain** for small T/P deviations

A scheme of the arrangement
of the GEM inside the test
chamber.

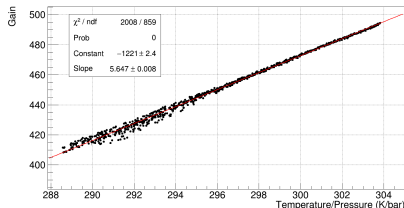




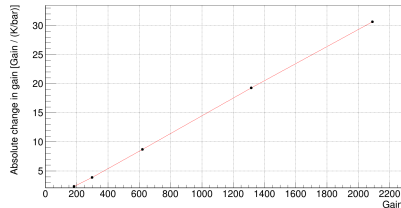
Gain vs. time

- MCA spectra with **1 minute-intervals**
- 2% overshooting of gain after 10V V_{GEM} increase
- Cut of first 150 minutes to get rid of charge up effects

Temperature/Pressure Correction



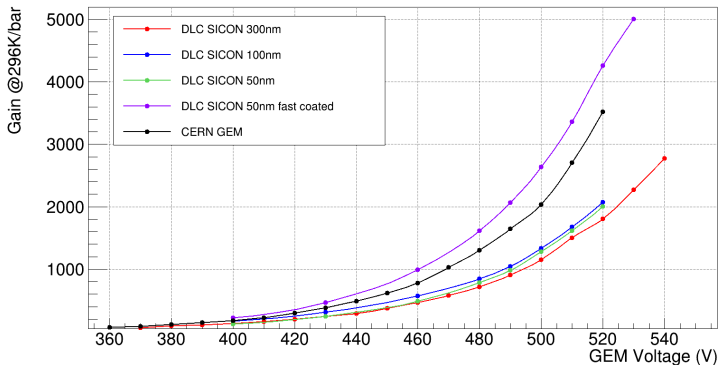
GEM gain vs. T/P at constant voltage



Absolute change in gain per 1 K/bar vs gain

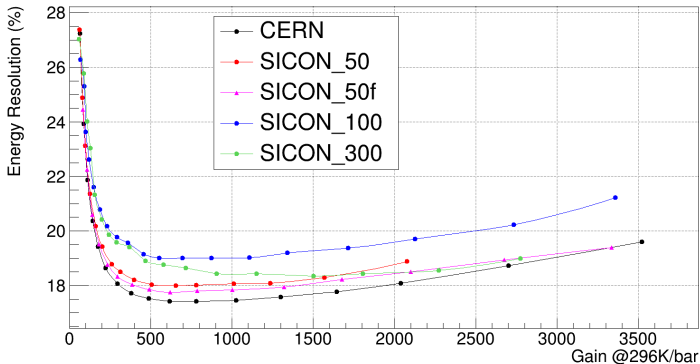
GEM	Coating speed	Thickness nm	Change in gain % / (K/bar)
CERN	–	0	1.39
SICON50f	fast	50	1.49
SICON50	normal	50	1.19
SICON100	normal	100	0.87
SICON300	normal	300	0.78

- Aim to get same conditions to compare the measurements.
- A simple T/P correction coefficient for each type of GEM independent on other parameters around 1 atm and 300 K



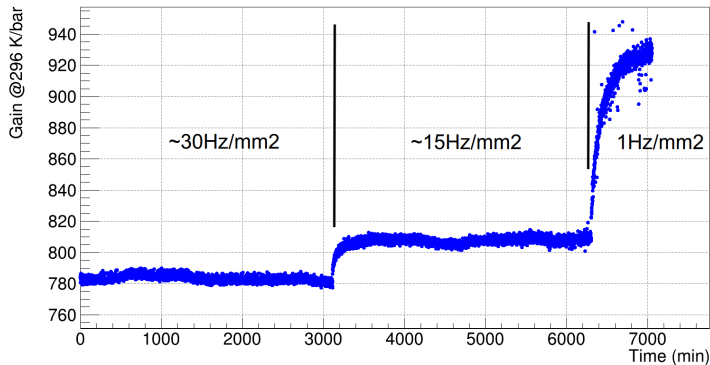
Gain vs. GEM Voltage for SICON GEMs.

- Each point: **Gaussian mean** of the distribution of at least 90 MCA spectra.
- With DLC coating, **lower gain than in CERN GEM is achieved at same voltage**, except **50nm fast coated DLC GEMs**.



Energy Resolution vs. gain for 50nm fast coated SICON GEMs.

- Each point: **Gaussian mean** of the distribution of at least 90 MCA spectra
- Similar energy resolutions with respect to CERN GEMs

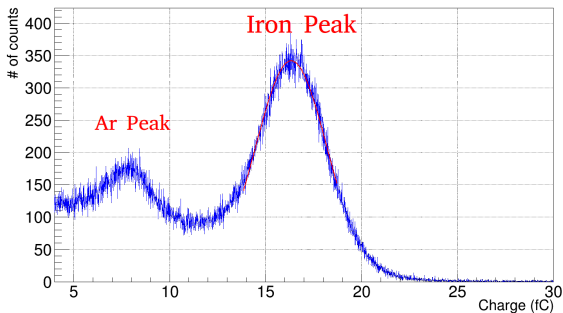


Gain vs. time with different rates for 50nm fast coated SICON GEMs.

- SICON GEM gain depends on the rate.
- The higher the rate, the lower the gain.
- Q: Typical behaviour of GEMs at lower rates??

- CERN GEMs have been DLC coated by PACVD method with 3 different thicknesses and 2 different coating speeds (**50nm fast coated, 50nm, 100nm, 300nm**).
- FIB analysis predicts the thickness for 50nm fast coated DLC GEMs as **~50nm on the surface**
- Existence of the DLC coating is confirmed **the inner wall of the holes** by EDX analysis
- Gains are corrected for **environmental parameters (pressure and temperature)**
- With DLC coating, **lower gain than in CERN GEM is achieved at same voltage**, except **50nm fast coated DLC GEMs**.
- **The thicker the coating, the lower the gain at same voltage.**
- SICON GEM gain depends on rate at lower values. (under investigation)

Backup



Signal with 2 peaks (Argon escape peak and ^{55}Fe peak).

- Number of primary electrons:

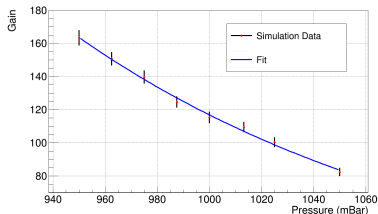
$$n_p = \frac{5900 \text{ eV}}{25 \text{ eV}} \times 0.80 + \frac{5900 \text{ eV}}{34 \text{ eV}} \times 0.20 = 223$$

▶ 25eV and 34eV : Average energy per ionization for Ar and CO₂ respectively.

- Thus, the gain: ratio of total (n_t) to primary (n_p) electron number

$$G = n_t \times \frac{1}{n_p} = \frac{Q_t}{e} \times \frac{1}{223}$$

- Assumption for gain adjustment:
 - $G = e^{\alpha x}$ is valid
 - $\alpha = Ape^{-Bp/E} \propto p$ is valid
- Pressure adjustment fit function: $G = e^{sp+c}$
 - s: slope
 - c: constant

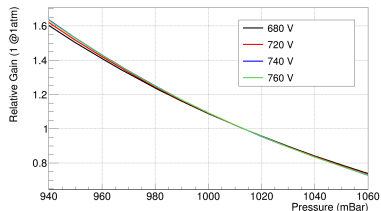


Fit on simulations of ceramic GEM at 740 V

- Gain adjustment (at 1 atm):

$$G_{corr} = \frac{G_{meas}(p)}{e^{sp+c}}$$

V_{GEM} (V)	slope (Bar^{-1})	constant
680	$-6.44 \pm 4.5\%$	$6.53 \pm 4.5\%$
720	$-6.59 \pm 4.4\%$	$6.68 \pm 4.4\%$
740	$-6.72 \pm 4.5\%$	$6.81 \pm 4.5\%$
760	$-6.69 \pm 4.8\%$	$6.78 \pm 4.8\%$



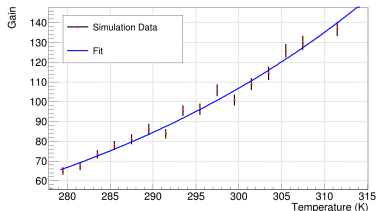
Fits on simulations of ceramic GEM at different V_{GEM}

- Adjustment function by fitting simulation data
- Temperature adjustment fit function: $G = e^{sT+c}$
 - ▶ s: slope
 - ▶ c: constant

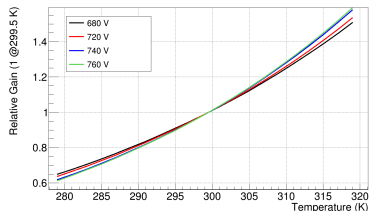
- Gain adjustment (at 299.5 K):

$$G_{corr} = \frac{G_{meas}(T)}{e^{sT+c}}$$

V_{GEM} (V)	slope ($10^2 K^{-1}$)	constant
680	$2.11 \pm 2.2\%$	$-6.32 \pm 2.2\%$
720	$2.2 \pm 2.1\%$	$-6.59 \pm 2.1\%$
740	$2.35 \pm 3\%$	$-7.03 \pm 3\%$
760	$2.39 \pm 5.4\%$	$-7.15 \pm 5.4\%$



Fit on simulations of ceramic GEM
at 740 V



Fits on simulations of ceramic
GEM at different V_{GEM}

- The gas system includes a gas mixing system with desired percentages and a small chamber to monitor gas stabilization inside the experimental chamber
- After mixing process, gas mixture flows through the test chamber and/or the TPC prototype
- Later, the gas mixture flows to another chamber where we can monitor gas stabilization before it is released to air.

